Revised August 2000

## **CD4023BC Buffered Triple 3-Input NAND Gate**

#### **General Description**

FAIRCHILD

SEMICONDUCTOR

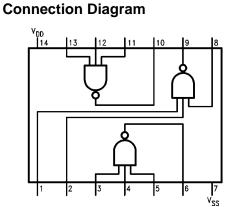
These triple gates are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and Pchannel enhancement mode transistors. They have equal source and sink current capabilities and conform to standard B series output drive. The devices also have buffered outputs which improve transfer characteristics by providing very high gain. All inputs are protected against static discharge with diodes to  $V_{DD}$  and  $V_{SS}$ .

#### **Features**

- Wide supply voltage range: 3.0V to 15V
- High noise immunity: 0.45 V<sub>DD</sub> (typ)
- Low power TTL compatibility:
- fan out of 2 driving 74L or 1 driving 74LS ■ 5V–10V–15V parametric ratings
- Symmetrical output characteristics
- Maximum input leakage 1 µA at 15V over full temperature range

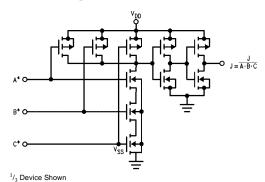
#### **Ordering Code:**

Order Number	Package Number	Package Description
CD4023BCM	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
CD4023BCS	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
CD4023BCN	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide



Top View

#### **Block Diagram**



\*All Inputs Protected by Standard CMOS Input Protection Circuit.

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#### Absolute Maximum Ratings(Note 1) (Note 2)

DC Supply Voltage (V <sub>DD</sub> )	–0.5 $V_{DC}$ to +18 $V_{DC}$
Input Voltage (V <sub>IN</sub> )	–0.5 $V_{DC}$ to $V_{DD} \mbox{+} 0.5 \ V_{DC}$
Storage Temp. Range (T <sub>S</sub> )	-65°C to +150°C
Power Dissipation (P <sub>D</sub> )	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T <sub>L</sub> )	
(Soldering, 10 seconds)	260°C

# Recommended Operating Conditions

DC Supply Voltage (V<sub>DD</sub>) Input Voltage (V<sub>IN</sub>) Operating Temperature Range (T<sub>A</sub>)

 $\begin{array}{c} 5 \ V_{DC} \ to \ 15 \ V_{DC} \\ 0 \ V_{DC} \ to \ V_{DD} \ V_{DC} \\ -40^\circ C \ to \ +85^\circ C \end{array}$ 

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2:  $V_{SS} = 0V$  unless otherwise specified.

### DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	<b>−40°C</b>		+25°C			+85°C		Units
Symbol	Falameter	Conditions	Min	Тур	Min	Тур	Max	Min	Max	Units
I <sub>DD</sub>	Quiescent Device Current	$V_{DD} = 5V$		1.0		0.004	1.0		7.5	
		$V_{DD} = 10V$		2.0		0.005	2.0		15	μA
		$V_{DD} = 15V$		4.0		0.006	4.0		30	
V <sub>OL</sub>	LOW Level Output Voltage	$V_{DD} = 5V$		0.05		0	0.05		0.05	
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	
V <sub>OH</sub>	HIGH Level Output Voltage	$V_{DD} = 5V$	4.95		4.95	5		4.95		
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		
V <sub>IL</sub>	LOW Level Input Voltage	V <sub>DD</sub> =5V, V <sub>O</sub> =4.5V		1.5		2	1.5		1.5	
		V <sub>DD</sub> =10V, V <sub>O</sub> =9.0V  I <sub>O</sub>  <1µA		3.0		4	3.0		3.0	V
		V <sub>DD</sub> =15V, V <sub>O</sub> =13.5V		4.0		6	4.0		4.0	
VIH	HIGH Level Input Voltage	V <sub>DD</sub> =5V, V <sub>O</sub> =0.5V	3.5		3.5	3		3.5		
		$V_{DD}$ =10V, $V_{O}$ =1.0V  I_{O} <1\mu A	7.0		7.0	6		7.0		V
		V <sub>DD</sub> =15V, V <sub>O</sub> =1.5V	11.0		11.0	9		11.0		
l <sub>OL</sub>	LOW Level Output Current	$V_{DD} = 5V, V_{O} = 0.4V$	0.52		0.44	0.88		0.36		
	(Note 4)	$V_{DD} = 10V, V_{O} = 0.5V$	1.3		1.1	2.2		0.90		mA
		$V_{DD} = 15V, V_{O} = 1.5V$	3.6		3.0	8		2.4		
I <sub>OH</sub>	HIGH Level Output Current	$V_{DD} = 5V, V_{O} = 4.6V$	-0.52		-0.44	-0.88		-0.36		
	(Note 4)	$V_{DD} = 10V, V_{O} = 9.5V$	-1.3		-1.1	-2.2		-0.90		mA
		$V_{DD} = 15V, V_{O} = 13.5V$	-3.6		-3.0	-8		-2.4		
I <sub>IN</sub>	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		-0.3		-10 <sup>-5</sup>	-0.3		-1.0	μA
		$V_{DD} = 15V, V_{IN} = 15V$		0.3		10 <sup>-5</sup>	0.3		1.0	μΛ

Note 3:  $V_{SS} = 0V$  unless otherwise specified.

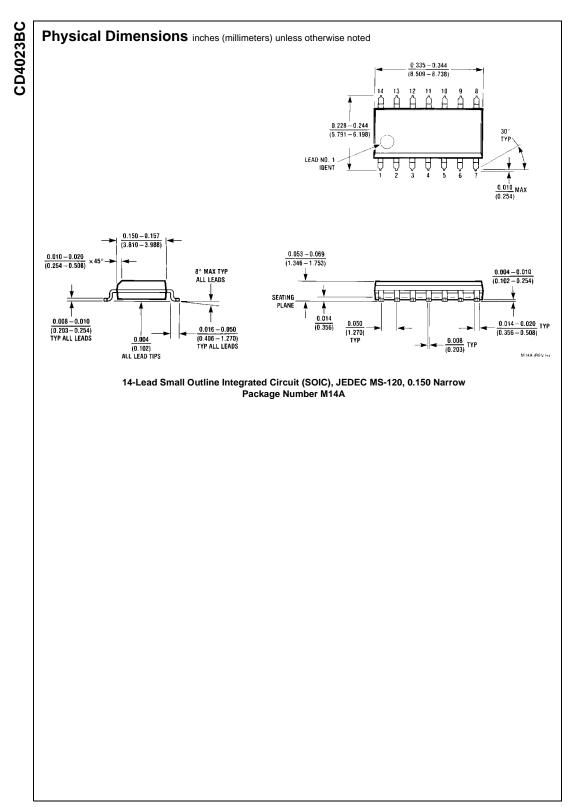
Note 4:  $I_{OH}$  and  $I_{OL}$  are tested one output at a time.

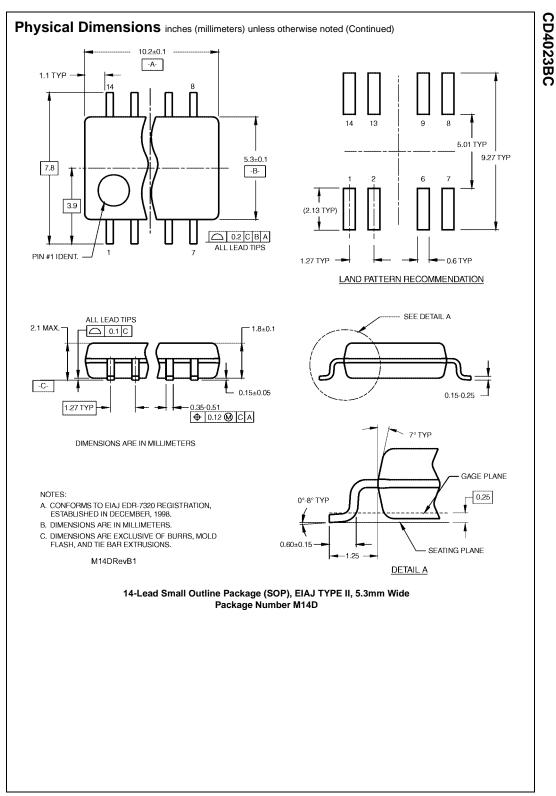
	C, $C_L = 50 \text{ pF}$ , $R_L = 200 \text{k}$ , unless otherwise speci	liou				
Symbol	Parameter	Conditions	Min	Тур	Max	Units
t <sub>PHL</sub> F	Propagation Delay, HIGH-to-LOW Level	$V_{DD} = 5V$		130	250	
		$V_{DD} = 10V$		60	100	ns
		$V_{DD} = 15V$		40	70	
t <sub>PLH</sub>	Propagation Delay, LOW-to-HIGH Level	$V_{DD} = 5V$		110	250	
		$V_{DD} = 10V$		50	100	ns
		$V_{DD} = 15V$		35	70	
t <sub>THL</sub> ,	Transition Time	$V_{DD} = 5V$		90	200	
t <sub>TLH</sub>		$V_{DD} = 10V$		50	100	ns
		$V_{DD} = 15V$		40	80	
C <sub>IN</sub>	Average Input Capacitance	Any Input		5	7.5	pF
CPD	Power Dissipation Capacity (Note 6)	Any Gate		17		pF

Note 5: AC Parameters are guaranteed by DC correlated testing.

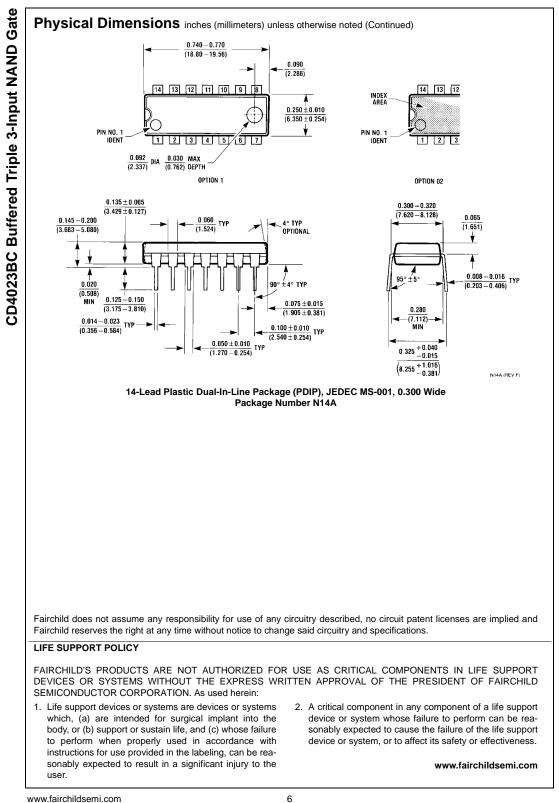
Note 6:  $C_{PD}$  determines the no load AC power consumption of any CMOS device. For complete explanation, see Family Characteristics Application Note AN-90.

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